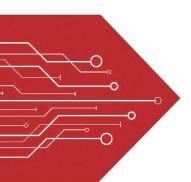
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet







1. BASE

SOT - 23

2. EMITTER

3. COLLECTOR

FMMT495 TRANSISTOR (NPN)

FEATURE

- Low V_{CE(sat)}
- h_{FE} characterised up to 1A for high current gain hold up
- For general amplification

MARKING: 495

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	170	V
V _{CEO}	Collector-Emitter Voltage	150	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current	1	Α
Pc	Collector Power Dissipation	250	mW
R _{OJA}	Thermal Resistance from Junction to Ambient	500	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55∼+150	$^{\circ}$

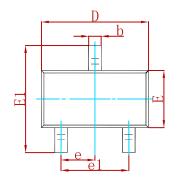
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

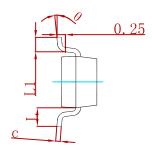
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	170			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =10mA, I _B =0	150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =150V, I _E =0			0.1	μA
Collector cut-off current	I _{CES}	V _{CE} =150V,V _{BE} =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μA
	h _{FE(1)} *	V _{CE} =10V, I _C =1mA	100			
DC ourrent sein	h _{FE(2)} *	V _{CE} =10V, I _C =250mA	100		300	
DC current gain	h _{FE(3)} *	V _{CE} =10V, I _C =500mA	50			
	h _{FE(4)} *	V _{CE} =10V, I _C =1A	10			
Callegter emitter esturation values	V _{CE(sat)(1)} *	I _C =250mA, I _B =25mA			0.2	V
Collector-emitter saturation voltage	V _{CE(sat)(2)} *	I _C =500mA, I _B =50mA			0.3	V
Base-emitter turn-on voltage	V _{BE(on)} *	V _{CE} =10V, I _C =500mA			1	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =500mA, I _B =50mA			1	V
Transition frequency	f _T	V _{CE} =10V,I _C =50mA,f=100MHz	100			MHz
Collector output capacitance	Cob	Vcb=10V,IE=0,f=1MHz			10	pF

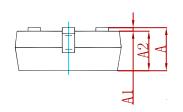
^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



PACKAGE MECHANICAL DATA

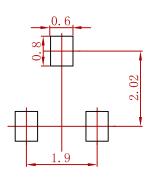






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Зупівої	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
Ĺ	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
FMMT495	SOT-23	3000



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